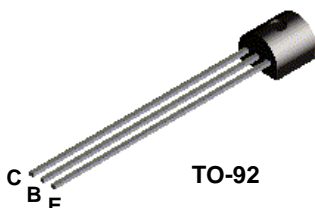


## 2N3905



### PNP General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 100 mA.

#### Absolute Maximum Ratings\*

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	40	V
V <sub>CB0</sub>	Collector-Base Voltage	40	V
V <sub>EBO</sub>	Emitter-Base Voltage	5.0	V
I <sub>C</sub>	Collector Current - Continuous	200	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

\*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

#### NOTES:

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

#### Thermal Characteristics

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		2N3905	
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	625	mW
		5.0	mW/°C
R <sub>θJC</sub>	Thermal Resistance, Junction to Case	83.3	°C/W
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient	200	°C/W

# PNP General Purpose Amplifier

(continued)

2N3905

## Electrical Characteristics

TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
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### OFF CHARACTERISTICS

$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage*	$I_C = 1.0 \text{ mA}, I_B = 0$	40		V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 10 \text{ } \mu\text{A}, I_E = 0$	40		V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10 \text{ } \mu\text{A}, I_C = 0$	5.0		V
$I_{CEX}$	Collector Cutoff Current	$V_{CE} = 30 \text{ V}, V_{OB} = 3.0 \text{ V}$		50	nA
$I_{BL}$	Base Cutoff Current	$V_{CE} = 30 \text{ V}, V_{OB} = 3.0 \text{ V}$		50	nA

### ON CHARACTERISTICS\*

$h_{FE}$	DC Current Gain	$V_{CE} = 1.0 \text{ V}, I_C = 0.1 \text{ mA}$ $V_{CE} = 1.0 \text{ V}, I_C = 1.0 \text{ mA}$ $V_{CE} = 1.0 \text{ V}, I_C = 10 \text{ mA}$ $V_{CE} = 1.0 \text{ V}, I_C = 50 \text{ mA}$ $V_{CE} = 1.0 \text{ V}, I_C = 100 \text{ mA}$	30 40 50 30 15	150	
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$		0.25 0.40	V V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 50 \text{ mA}, I_B = 5.0 \text{ mA}$	0.65	0.85 0.95	V V

### SMALL SIGNAL CHARACTERISTICS

$C_{ob}$	Output Capacitance	$V_{CB} = 5.0 \text{ V}, f = 1.0 \text{ MHz}$		4.5	pF
$C_{ib}$	Input Capacitance	$V_{EB} = 0.5 \text{ V}, f = 1.0 \text{ MHz}$		10	pF
$h_{fe}$	Small-Signal Current Gain	$I_C = 10 \text{ mA}, V_{CE} = 20 \text{ V},$ $f = 100 \text{ MHz}$	2.0		
$h_{fe}$	Small-Signal Current Gain	$I_C = 1.0 \text{ mA}, V_{CE} = 10 \text{ V},$	50	200	
$h_{fe}$	Voltage Feedback Ratio	$f = 1.0 \text{ KHz}$	0.1	5.0	$\times 10^{-4}$
$h_{ie}$	Input Impedance		0.5	8.0	k $\Omega$
$h_{oe}$	Output Impedance		1.0	40	$\mu\text{mhos}$
NF	Noise Figure	$V_{CE} = 5.0 \text{ V}, I_C = 100 \text{ } \mu\text{A},$ $R_S = 1.0 \text{ k}\Omega,$ $B_W = 10 \text{ Hz to } 15.7 \text{ KHz}$		5.0	dB

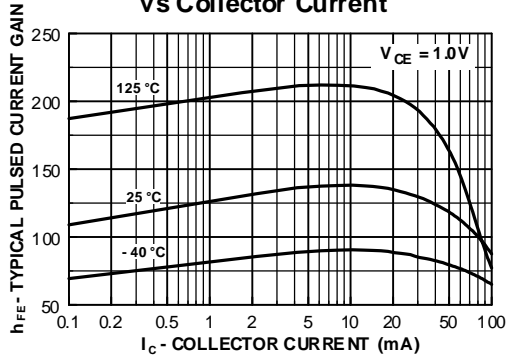
### SWITCHING CHARACTERISTICS

$t_d$	Delay Time	$V_{CC} = 3.0 \text{ V}, I_{CS} = 10 \text{ mA},$		35	ns
$t_r$	Rise Time	$I_{B1} = 1.0 \text{ mA}, V_{OB(off)} = 3.0 \text{ V}$		35	ns
$t_s$	Storage Time	$V_{CC} = 3.0 \text{ V}, I_{CS} = 10 \text{ mA},$		200	ns
$t_f$	Fall Time	$I_{B1} = I_{B2} = 1.0 \text{ mA}$		60	ns

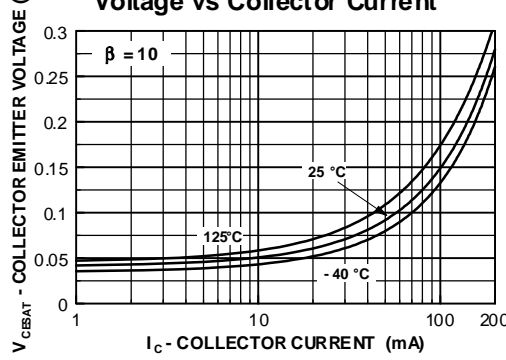
\*Pulse Test: Pulse Width  $\leq 300 \text{ } \mu\text{s}$ , Duty Cycle  $\leq 2.0\%$

Typical Characteristics

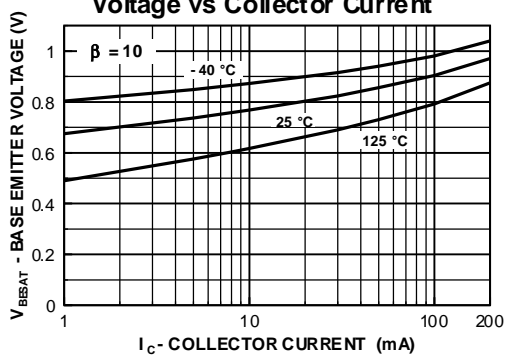
Typical Pulsed Current Gain vs Collector Current



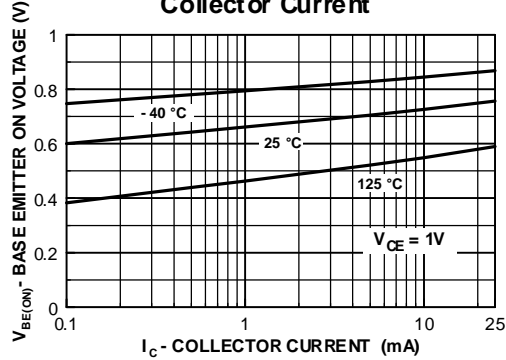
Collector-Emitter Saturation Voltage vs Collector Current



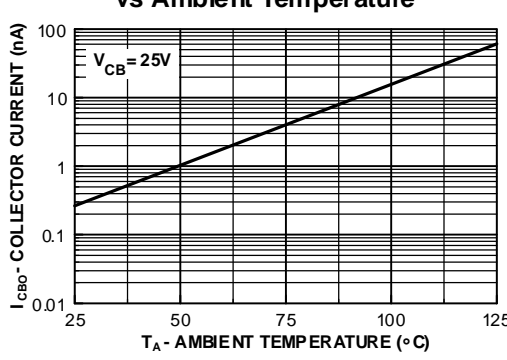
Base-Emitter Saturation Voltage vs Collector Current



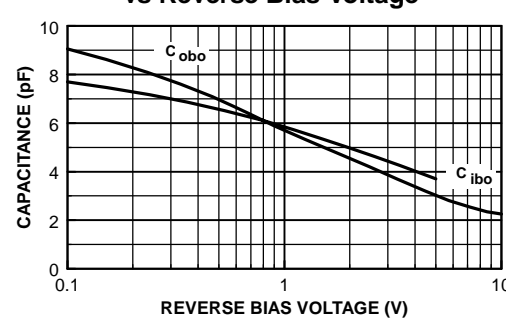
Base Emitter ON Voltage vs Collector Current



Collector-Cutoff Current vs Ambient Temperature

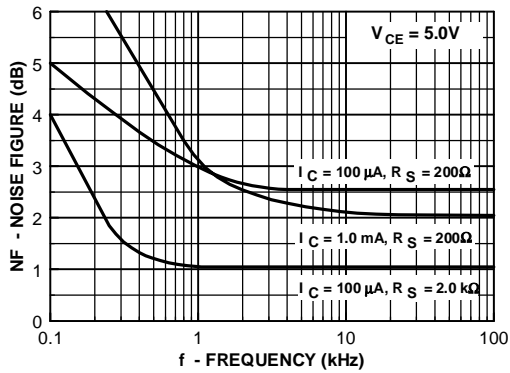


Common-Base Open Circuit Input and Output Capacitance vs Reverse Bias Voltage

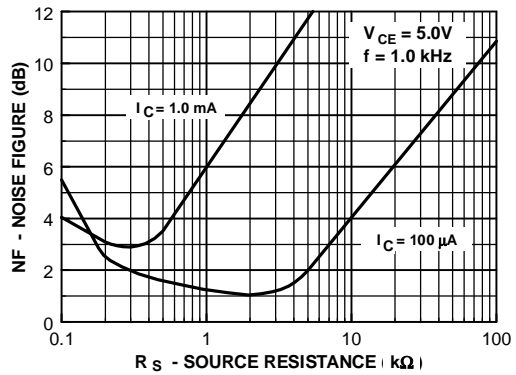


Typical Characteristics (continued)

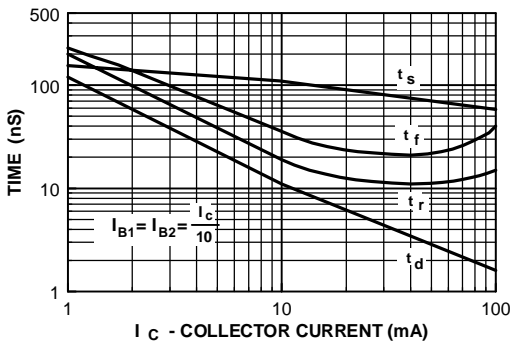
Noise Figure vs Frequency



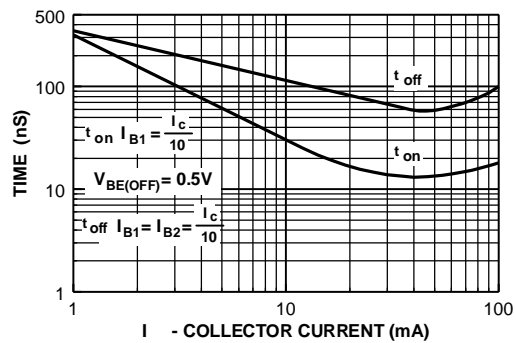
Noise Figure vs Source Resistance



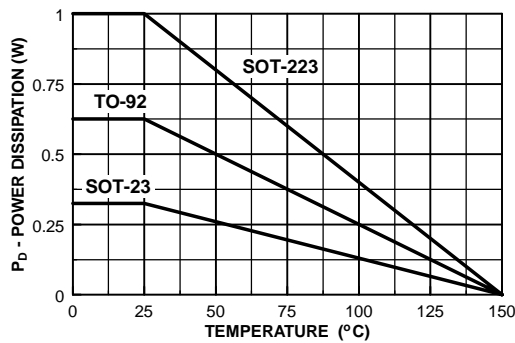
Switching Times vs Collector Current



Turn On and Turn Off Times vs Collector Current

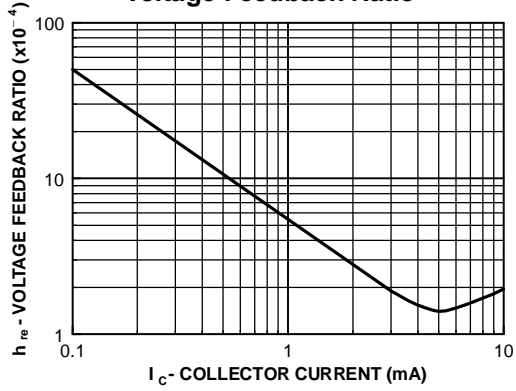


Power Dissipation vs Ambient Temperature

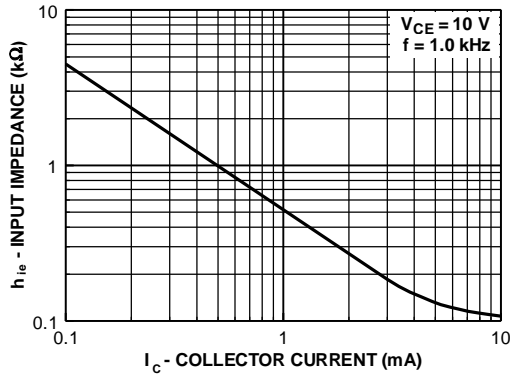


Typical Characteristics (continued)

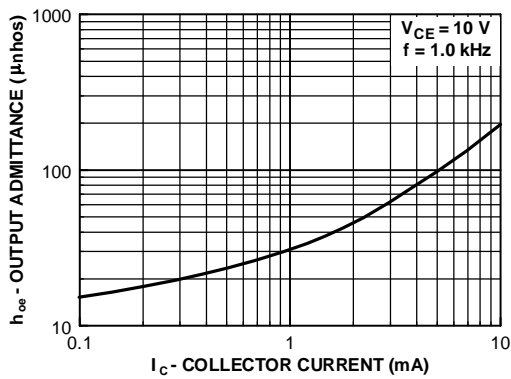
Voltage Feedback Ratio



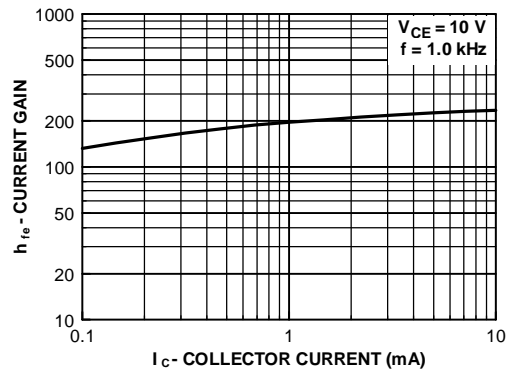
Input Impedance



Output Admittance



Current Gain



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